

KWD10

RELIABILITY DATA

信頼性データ

No. RD-08T-646A		
承認	査閲	担当
Kinosawa 31.Oct.'08	Y.Kihama 30.Oct.'08	M.Nagai 30.Oct.'08

I N D E X

	PAGE
1. M T B F 計算値 Calculated Values of MTBF	2/40
2. 部品ディレーティング Component Derating	3/40～6/40
3. 部品温度上昇値 Components Temperature Rise ΔT List	7/40
4. 電解コンデンサ推定寿命計算値 Electrolytic Capacitor Lifetime Versus Load	8/40～17/40
5. アブノーマル試験 Abnormal Test	18/40～32/40
6. 振動試験 Vibration Test	33/40～34/40
7. ノイズシミュレート試験 Noise Simulate Test	35/40
8. 静電気シミュレート試験 Electro-Static Discharge Test	36/40
9. 雷サージ試験 Impulse Test	37/40
10. 雑音端子電圧 EMI Test	38/40～40/40

※信頼性試験は代表データであり、この値は実力値とお考え願います。

※本データに掲載してあります内蔵部品の名称は、本製品を開発した当初のものです。

これらは改善等の為に変更されている可能性もありますが、ご了承下さい。

The following data are typical values and the data to be considered as ability values.
 The built-in components names on this data are the things the time of Development.
 Please understand that it may be changed for an improvement etc.

M . T . B . F

1. Method of calculation

This calculation is by the components count method laid down by the DC Stabilized Power Supplies (Switching mode) committee of EIAJ.

The MTBF is determined by means of a fixed component failure rate λ_c given to each component and the number of component count of each type of component. λ_c is determined based on MIL-HDBK-217D.

Please refer to the EIAJ handbook no. RCF-9021 for detail.

Formula:

$$\text{MTBF} = \frac{1}{\lambda_{\text{equip}}} = \frac{1}{\sum_{i=1}^n N_i(\lambda_c)_i} \times 10^6 \quad (\text{Hrs})$$

λ_{equip} = Total equipment failure rate (Failures/ 10^6 hrs)

λ_c = Failure rate of the i^{th} component

N_i = Number of i^{th} component

n = Number of categories of components

2. MTBF Value

Temperature 25°C

MTBF = 84,877 hrs.

Components Derating Data(At Nominal Line and Rated Load, Ambient Temperature 50°C)Calculation Method**A. Semiconductors**

The derating factor is taken as the ratio of the actual operating junction temperature taking into consideration operating ambient temperature, power loss and thermal resistance to the maximum rated junction temperature specifications of the components.

B. IC, Resistors, Capacitors etc.

Operating ambient temperature, operating condition, power loss for each individual component are all designed to meet the requirements of Nemic-Lambda's design standard.

C. Thermal Resistance Calculation

$$\theta_{jc} = \frac{T_j(\max) - T_c}{P_c(\max)}$$

$$\theta_{ja} = \frac{T_j(\max) - T_a}{P_c(\max)}$$

T_c : Case Temperature (Normally 25°C)

T_a : Ambient Temperature (Normally 25°C)

P_{c(max)} : Maximum Power Loss

T_{j(max)} : Maximum Junction Temperature

θ_{jc} : Junction to Case Thermal Resistance

θ_{ja} : Junction to ambient Thermal Resistance

認 APPD	.	設計 ENGR	.	図面番号 DWG-No.
.	.			PA774-56-02 - □
検 CHK	.	製 DWG	.	

SEMICONDUCTOR DERATING

DWG. NO. : PA774-56-03

DATE : 6-DEC-92

MODEL : KWD10-1212

VIN = AC 100V

LOAD = 100%

Ta = 50°C

Q1 2SK1510 FUJI	Tchmax = 150 °C $\Theta_{ch-c} = 1.563 \text{ }^{\circ}\text{C/W}$ Pdmax = 80 W
	Pd = 0.365 W $\Delta T_c = 47.9 \text{ }^{\circ}\text{C}$ Tc = 97.9 °C
	Tj = Tc + (Θ_{ch-c}) * Pd = 98.5 °C
	D.F. = 65.6 %
Q2 2SC2873-Y TOSHIBA	Tjmax = 150 °C $\Theta_{j-c} = 125 \text{ }^{\circ}\text{C/W}$ Pdmax = 1 W
	Pd = 0.0 W $\Delta T_c = 39.1 \text{ }^{\circ}\text{C}$ Tc = 89.1 °C
	Tj = Tc + (Θ_{j-c}) * Pd = 89.1 °C
	D.F. = 59.4 %
A1 UC2842ADW UNITRODE	Tjmax = 150 °C $\Theta_{j-c} = 70 \text{ }^{\circ}\text{C/W}$ Pdmax = 0.725 W
	Pd = 0.38 W $\Delta T_c = 49.4 \text{ }^{\circ}\text{C}$ Tc = 99.4 °C
	Tj = Tc + (Θ_{j-c}) * Pd = 126.0 °C
	D.F. = 84.0 %
A2 HA17431UA HITACHI	Tjmax = 125 °C $\Theta_{j-c} = 259.7 \text{ }^{\circ}\text{C/W}$ Pdmax = 0.385 W
	Pd = 21 mW $\Delta T_c = 38.9 \text{ }^{\circ}\text{C}$ Tc = 88.9 °C
	Tj = Tc + (Θ_{j-c}) * Pd = 94.4 °C
	D.F. = 75.5 %
PC1 (LED) TLP121GR TOSHIBA	Tjmax = 125 °C $\Theta_{j-c} = 400 \text{ }^{\circ}\text{C/W}$ Pdmax = 50 mW
	If = 1.8 mA $\Delta T_c = 38.5 \text{ }^{\circ}\text{C}$ Tc = 88.5 °C
	ALLOWABLE If (max) = 26.0 mA (at 88.5 °C)
	D.F. = 6.9 %
PC1 (TRANSISTOR) TLP121GR TOSHIBA	Tjmax = 125 °C $\Theta_{j-c} = 400 \text{ }^{\circ}\text{C/W}$ Pdmax = 150 mW
	Pd = 5.2 mW $\Delta T_c = 38.5 \text{ }^{\circ}\text{C}$ Tc = 88.5 °C
	Tj = Tc + (Θ_{j-c}) * Pd = 90.6 °C
	D.F. = 72.5 %
D1 S1WB(A)60B SHINDENGEN	Tjmax = 150 °C $\Theta_{j-l} = 10 \text{ }^{\circ}\text{C/W}$ Pdmax = 12.5 W
	Pd = 0.206 W $\Delta T_l = 34.6 \text{ }^{\circ}\text{C}$ T(lead) = 84.6 °C
	Tj = Tl + (Θ_{j-l}) * Pd = 86.7 °C
	D.F. = 57.8 %

SEMICONDUCTOR DERATING

DWG. NO. : PA774-56-04

DATE : 6-DEC-92

MODEL : KWD10-1212

VIN = AC 100V

LOAD = 100%

Ta = 50°C

D2 EC8FS6 NIHON-INTER	T _{jmax} = 150 °C Θ _{j-I} = 23 °C/W P _{dmax} = 5.43 W P _d = 30 mW Δ T _I = 48.7 °C T(lead) = 98.7 °C T _j = T _I + (Θ _{j-I}) * P _d = 99.4 °C D.F. = 66.3 %
D3 1SS184TE85L TOSHIBA	T _{jmax} = 125 °C Θ _{j-I} = 100 °C/W P _{dmax} = 150 mW P _d = 0.0 W Δ T _I = 45.7 °C T(lead) = 95.7 °C T _j = T _I + (Θ _{j-I}) * P _d = 95.7 °C D.F. = 76.6 %
D4 1SS184TE85L TOSHIBA	T _{jmax} = 125 °C Θ _{j-I} = 100 °C/W P _{dmax} = 150 mW P _d = 5.23 mW Δ T _I = 46.3 °C T(lead) = 96.3 °C T _j = T _I + (Θ _{j-I}) * P _d = 96.8 °C D.F. = 77.5 %
D5 D1FL20U SHINDENGEN	T _{jmax} = 150 °C Θ _{j-I} = 23 °C/W P _{dmax} = 5.43 W P _d = 27.28 mW Δ T _I = 48.7 °C T(lead) = 98.7 °C T _j = T _I + (Θ _{j-I}) * P _d = 99.3 °C D.F. = 66.2 %
D6 D1FL20U SHINDENGEN	T _{jmax} = 150 °C Θ _{j-I} = 23 °C/W P _{dmax} = 5.43 W P _d = 0.219 W Δ T _I = 55.4 °C T(lead) = 105.4 °C T _j = T _I + (Θ _{j-I}) * P _d = 110.4 °C D.F. = 73.6 %
D7 D1FL20U SHINDENGEN	T _{jmax} = 150 °C Θ _{j-I} = 23 °C/W P _{dmax} = 5.43 W P _d = 0.219 W Δ T _I = 55.4 °C T(lead) = 105.4 °C T _j = T _I + (Θ _{j-I}) * P _d = 110.4 °C D.F. = 73.6 %
D10 D1FL20U SHINDENGEN	T _{jmax} = 150 °C Θ _{j-I} = 23 °C/W P _{dmax} = 5.43 W P _d = 0.219 W Δ T _I = 54.3 °C T(lead) = 104.3 °C T _j = T _I + (Θ _{j-I}) * P _d = 109.3 °C D.F. = 72.9 %

SEMICONDUCTOR DERATING

DWG. NO. : PA774-56-05

DATE : 6-DEC-92

MODEL : KWD10-1212

VIN = AC 100V

LOAD = 100%

Ta = 50°C

D11 D1FL20U SHINDENGEN	Tjmax = 150 °C	Θj-I = 23 °C/W	Pdmax = 5.43 W
	Pd = 0.219 W	Δ Tl = 54.3 °C	T(lead) = 104.3 °C
	Tj = Tl + (Θj-I)*Pd =		109.3 °C
	D.F. = 72.9 %		
ZD1 1N4744A MOTOROLA	Tjmax = 200 °C	Θj-I = 175 °C/W	Pdmax = 1 W
	Pd = 0.0 W	Δ Tl = 35.4 °C	T(lead) = 85.4 °C
	Tj = Tl + (Θj-I)*Pd =		85.4 °C
	D.F. = 42.7 %		
ZD2 02CZ12-Z TOSHIBA	Tjmax = 150 °C	Θj-I = 100 °C/W	Pdmax = 150 mW
	Pd = 21.6 mW	Δ Tl = 45.4 °C	T(lead) = 95.4 °C
	Tj = Tl + (Θj-I)*Pd =		97.6 °C
	D.F. = 65.0 %		

TDK-Lambda

7
40

dT TEMPERATURE RISE

DWG. NO.

PA774-66-02

MODEL : KWD10-1212

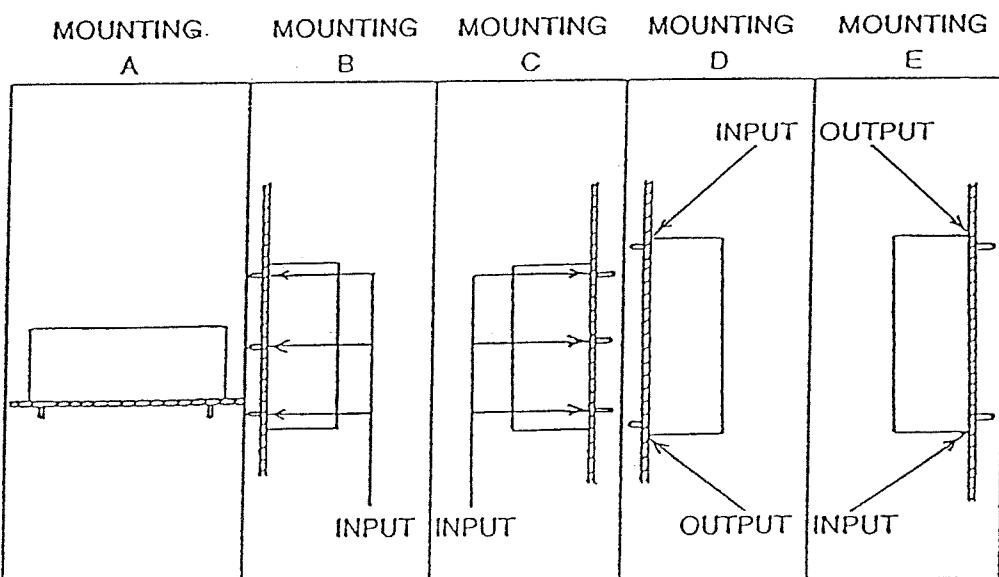
DATE : 31-DEC.-1992

INPUT VOLTAGE = 100VAC

Ta = 50 °C		dT TEMPERATURE RISE (°C)				
OUTPUT DERATING (%)		100%	100%	100%	100%	100%
SYMBOL	PARTS NAME	MOUNTING A	MOUNTING B	MOUNTING C	MOUNTING D	MOUNTING E
Q1	MOSFET	47.9	47.0	45.9	46.7	46.0
A1	PWM IC	49.4	48.9	46.4	48.2	46.3
D5	SBD	48.7	46.8	46.8	47.0	46.5
T1	X'TIMER	48.4	47.0	47.9	46.7	47.8
C6	E.CAP	38.8	39.1	36.6	37.8	37.4
C18	OS CAP.	41.0	39.8	39.8	38.8	41.7
C21	OS CAP.	39.0	38.8	37.3	37.0	39.6

INPUT VOLTAGE = 200VAC

Ta = 50 °C		dT TEMPERATURE RISE (°C)				
OUTPUT DERATING (%)		100%	100%	100%	100%	100%
SYMBOL	PARTS NAME	MOUNTING A	MOUNTING B	MOUNTING C	MOUNTING D	MOUNTING E
Q1	MOSFET	55.3	54.0	53.4	53.5	53.2
A1	PWM IC	53.8	52.9	50.8	52.5	50.8
D5	SBD	53.2	50.9	51.6	51.1	50.8
T1	X'TIMER	52.7	50.9	52.6	50.6	52.1
C6	E.CAP	43.1	43.4	41.2	42.0	42.0
C18	OS CAP.	44.0	42.6	43.1	41.4	45.0
C21	OS CAP.	42.2	41.7	40.6	39.7	43.0



ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

MODEL : KWD10-1212

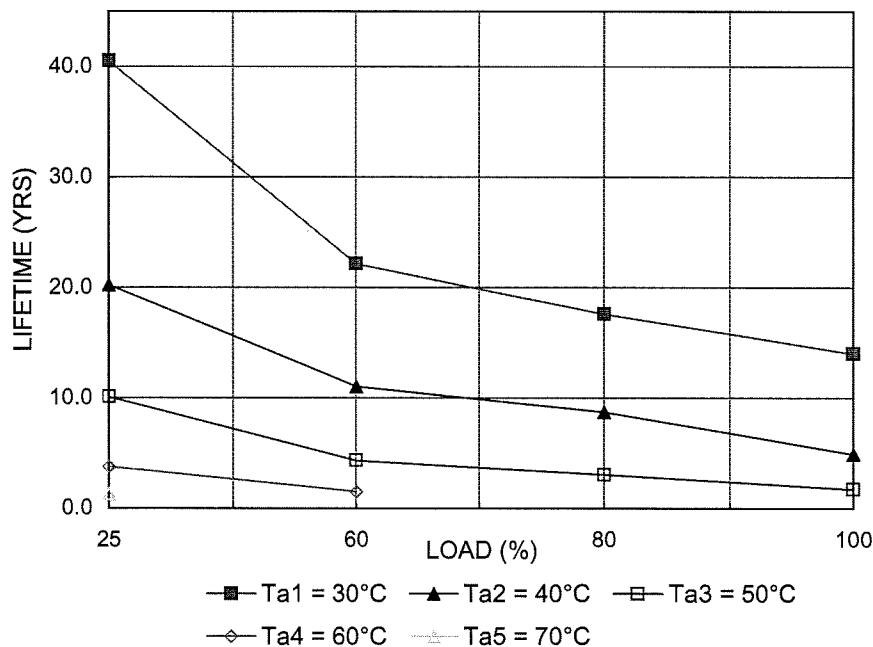
MOUNTING : A

VIN : 100VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	40.5	20.3	10.1	3.8	1.3
60	22.2	11.1	4.3	1.5	
80	17.6	8.8	3.1		
100	14.0	4.9	1.7		

GRAPH OF ELECTROLYTIC CAPACITOR LIFETIME VS LOAD
MOUNTING A KWD10-1212



計算式 FORMULA

1. アルミ電解コンデンサ
AL. Electrolytic capacitor

$$L = Lo \times 2^{(105-Tc)/10} \quad (\text{year})$$

L : 電解コンデンサ推定寿命計算値

Elec. Capacitor computed life.

(24 時間連続稼動、365 日)

(24 hrs per day, 365 days per year)

2. OSコンデンサ

O.S capacitor

$$L = Lo \times 10^{(105-Tc)/22} \quad (\text{year})$$

Lo :

電解コンデンサ保証寿命値

Guarantee life for Elec. cap.

電解コンデンサのケース温度

Case temperature of Elec. cap.

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

MODEL : KWD10-1212

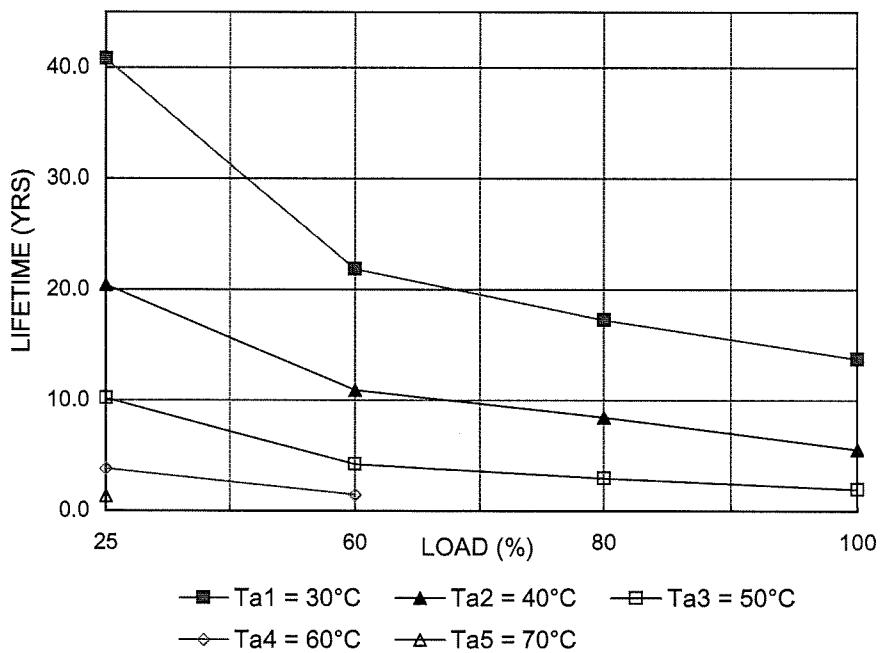
MOUNTING : B

VIN : 100VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	40.8	20.4	10.2	3.8	1.3
60	21.9	10.9	4.3	1.5	
80	17.3	8.5	3.0		
100	13.7	5.6	2.0		

GRAPH OF ELECTROLYTIC CAPACITOR LIFETIME VS LOAD
MOUNTING B KWD10-1212



計算式 FORMULA

1. アルミ電解コンデンサ

AL. Electrolytic capacitor

$$L = Lo \times 2^{(105-Tc)/10} \quad (\text{year})$$

L : 電解コンデンサ推定寿命計算値

Elec. Capacitor computed life.

(24 時間連続稼動、365 日)

(24 hrs per day, 365 days per year)

2. OSコンデンサ

O.S capacitor

$$L = Lo \times 10^{(105-Tc)/22} \quad (\text{year})$$

Lo : 電解コンデンサ保証寿命値

Guarantee life for Elec. cap.

Tc : 電解コンデンサのケース温度

Case temperature of Elec. cap.

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

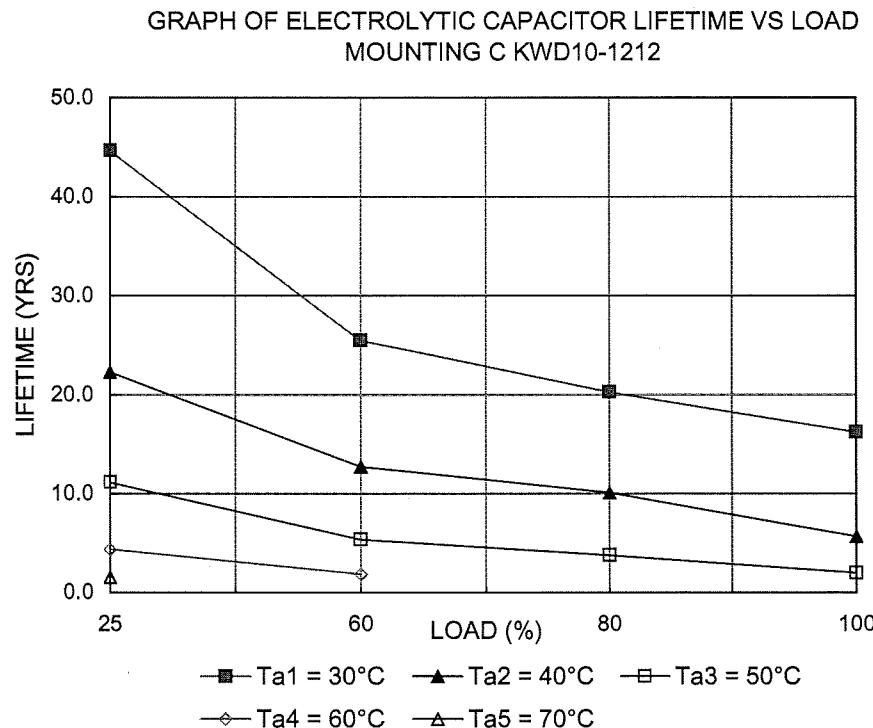
MODEL : KWD10-1212

MOUNTING : C

VIN : 100VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	44.7	22.3	11.2	4.4	1.5
60	25.5	12.7	5.4	1.9	
80	20.3	10.1	3.8		
100	16.2	5.7	2.0		



計算式 FORMULA

- | | | |
|--|--------|--|
| 1. アルミ電解コンデンサ
AL. Electrolytic capacitor
$L = Lo \times 2^{(105-Tc)/10}$ | L : | 電解コンデンサ推定寿命計算値
Elec. Capacitor computed life.
(24時間連続稼動、365日)
(24 hrs per day, 365 days per year) |
| 2. OSコンデンサ
O.S capacitor
$L = Lo \times 10^{(105-Tc)/22}$ | Lo : | 電解コンデンサ保証寿命値
Guarantee life for Elec. cap. |
| | Tc : | 電解コンデンサのケース温度
Case temperature of Elec. cap. |

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

MODEL : KWD10-1212

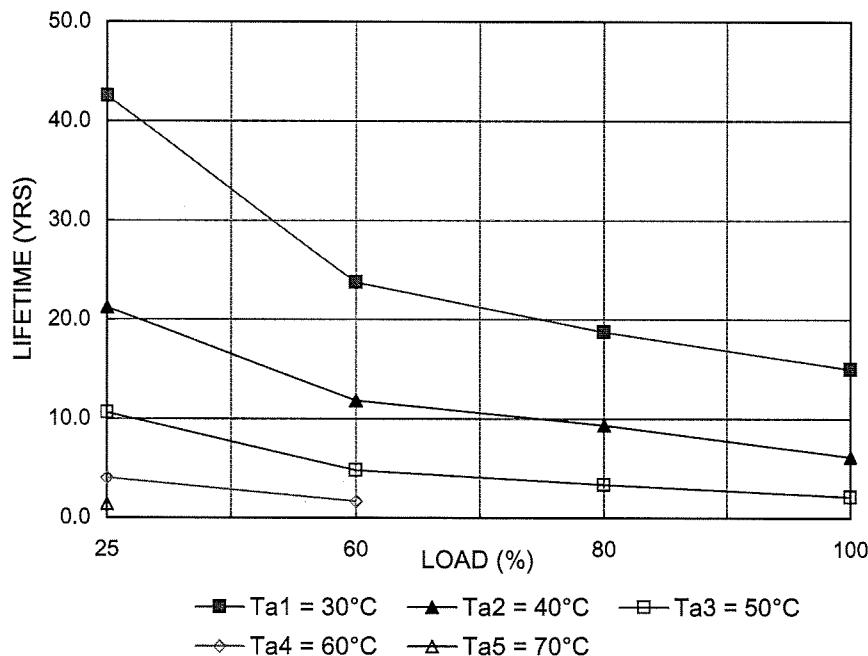
MOUNTING : D

VIN : 100VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	42.5	21.3	10.6	4.1	1.4
60	23.8	11.9	4.8	1.7	
80	18.8	9.4	3.4		
100	15.0	6.2	2.2		

GRAPH OF ELECTROLYTIC CAPACITOR LIFETIME VS LOAD
MOUNTING D KWD10-1212



計算式 FORMULA

1. アルミ電解コンデンサ
AL. Electrolytic capacitor
 $L = Lo \times 2^{(105-Tc)/10}$

L : 電解コンデンサ推定寿命計算値
Elec. Capacitor computed life.
(24時間連続稼動、365日)
(24 hrs per day, 365 days per year)

2. OSコンデンサ
O.S capacitor
 $L = Lo \times 10^{(105-Tc)/22}$

Lo : 電解コンデンサ保証寿命値
Guarantee life for Elec. cap.
 Tc : 電解コンデンサのケース温度
Case temperature of Elec. cap.

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

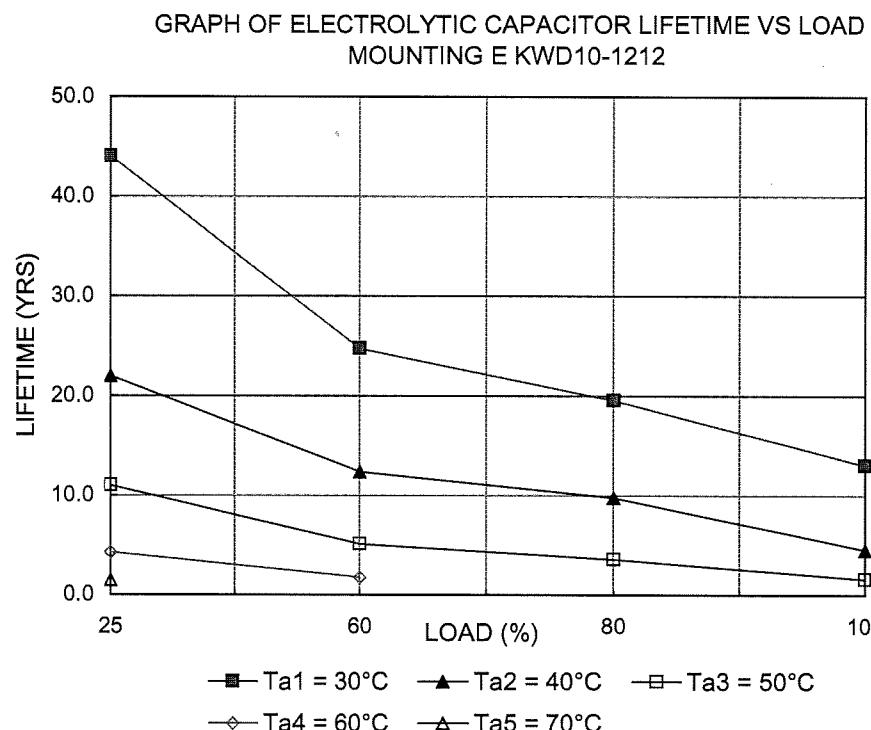
MODEL : KWD10-1212

MOUNTING : E

VIN : 100VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	44.0	22.0	11.0	4.3	1.5
60	24.8	12.4	5.1	1.8	
80	19.6	9.8	3.6		
100	13.0	4.6	1.6		



計算式 FORMULA

- | | |
|--|--|
| 1. アルミ電解コンデンサ
AL. Electrolytic capacitor
$L = Lo \times 2^{(105-Tc)/10}$ | L : 電解コンデンサ推定寿命計算値
Elec. Capacitor computed life.
(24時間連続稼動、365日)
(24 hrs per day, 365 days per year) |
| 2. OSコンデンサ
O.S capacitor
$L = Lo \times 10^{(105-Tc)/22}$ | Lo : 電解コンデンサ保証寿命値
Guarantee life for Elec. cap.
Tc : 電解コンデンサのケース温度
Case temperature of Elec. cap. |

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

MODEL : KWD10-1212

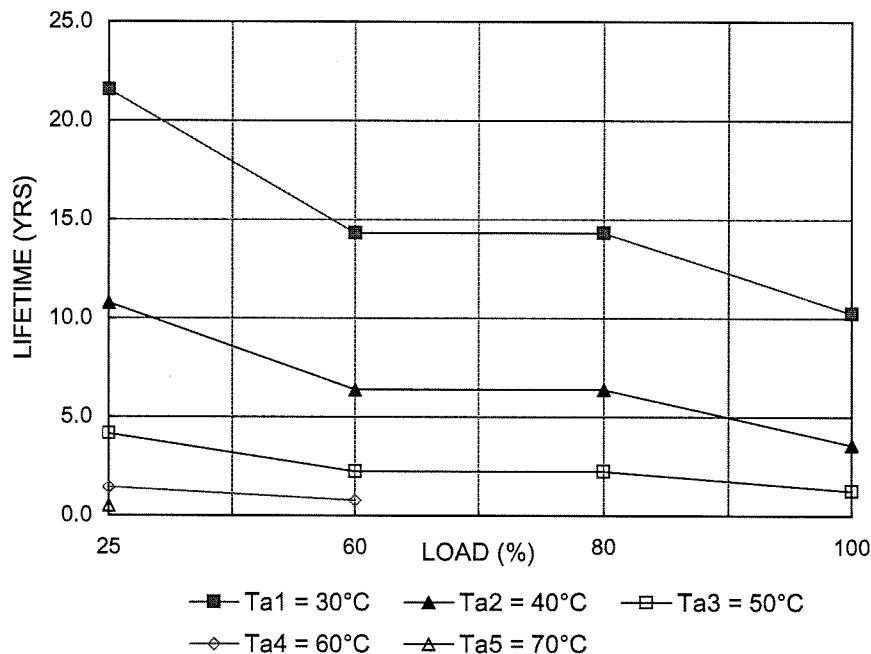
MOUNTING : A

VIN : 200VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	21.6	10.8	4.2	1.5	0.5
60	14.3	6.4	2.2	0.8	
80	14.3	6.4	2.2		
100	10.2	3.6	1.3		

GRAPH OF ELECTROLYTIC CAPACITOR LIFETIME VS LOAD
MOUNTING A KWD10-1212



計算式 FORMULA

1. アルミ電解コンデンサ
AL. Electrolytic capacitor

$$L = Lo \times 2^{(105-Tc)/10} \quad (\text{year})$$

L : 電解コンデンサ推定寿命計算値

Elec. Capacitor computed life.

(24 時間連続稼動、365 日)

(24 hrs per day, 365 days per year)

2. OSコンデンサ

O.S capacitor

$$L = Lo \times 10^{(105-Tc)/22} \quad (\text{year})$$

Lo :

電解コンデンサ保証寿命値

Guarantee life for Elec. cap.

電解コンデンサのケース温度

Case temperature of Elec. cap.

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

MODEL : KWD10-1212

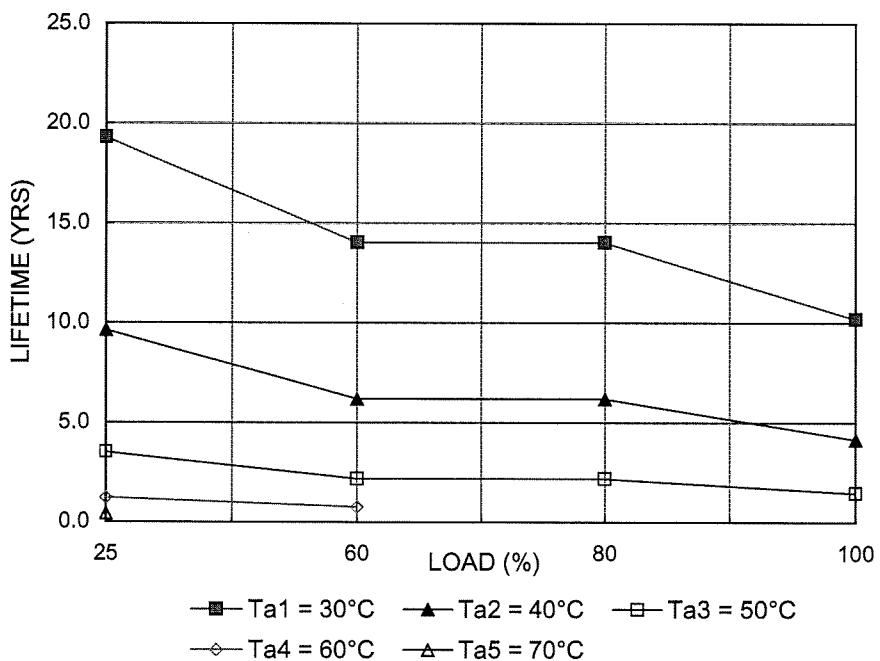
MOUNTING : B

VIN : 200VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	19.3	9.7	3.5	1.2	0.4
60	14.0	6.2	2.2	0.8	
80	14.0	6.2	2.2		
100	10.2	4.2	1.5		

GRAPH OF ELECTROLYTIC CAPACITOR LIFETIME VS LOAD
MOUNTING B KWD10-1212



計算式 FORMULA

1. アルミ電解コンデンサ
AL. Electrolytic capacitor

$$L = Lo \times 2^{(105-Tc)/10} \quad (\text{year})$$

L : 電解コンデンサ推定寿命計算値

Elec. Capacitor computed life.

(24時間連続稼動、365日)
(24 hrs per day, 365 days per year)

2. OSコンデンサ

O.S capacitor

$$L = Lo \times 10^{(105-Tc)/22} \quad (\text{year})$$

Lo :

電解コンデンサ保証寿命値

Guarantee life for Elec. cap.

電解コンデンサのケース温度

Case temperature of Elec. cap.

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

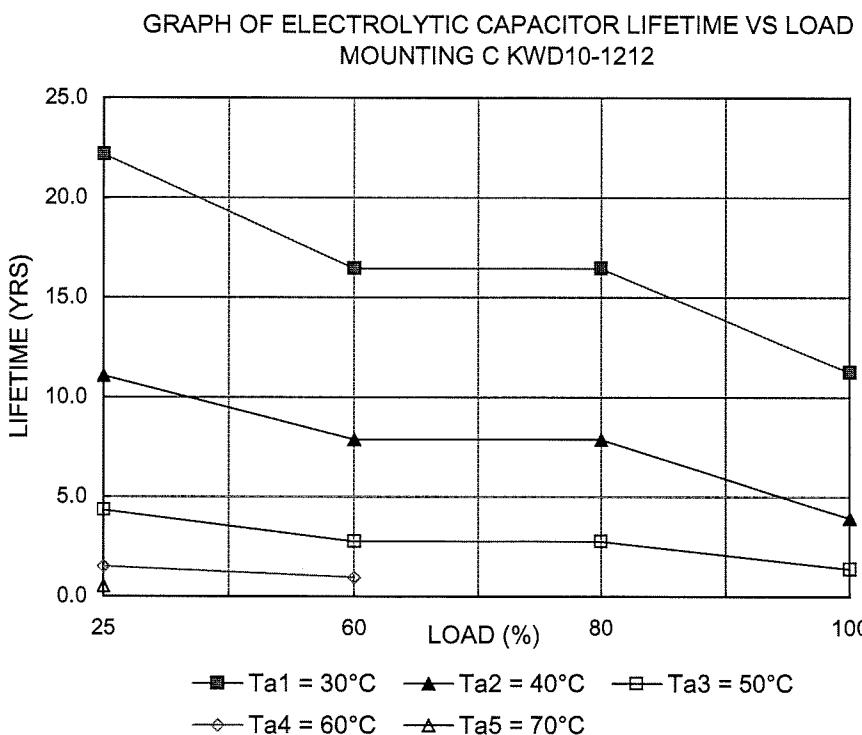
MODEL : KWD10-1212

MOUNTING : C

VIN : 200VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	22.2	11.1	4.3	1.5	0.5
60	16.5	7.9	2.8	1.0	
80	16.5	7.9	2.8		
100	11.3	4.0	1.4		



計算式 FORMULA

1. アルミ電解コンデンサ
AL. Electrolytic capacitor
 $L = Lo \times 2^{(105-Tc)/10}$

L : 電解コンデンサ推定寿命計算値
Elec. Capacitor computed life.
(24時間連続稼動、365日)
(24 hrs per day, 365 days per year)

2. OSコンデンサ
O.S capacitor
 $L = Lo \times 10^{(105-Tc)/22}$

Lo : 電解コンデンサ保証寿命値
Guarantee life for Elec. cap.
 Tc : 電解コンデンサのケース温度
Case temperature of Elec. cap.

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

MODEL : KWD10-1212

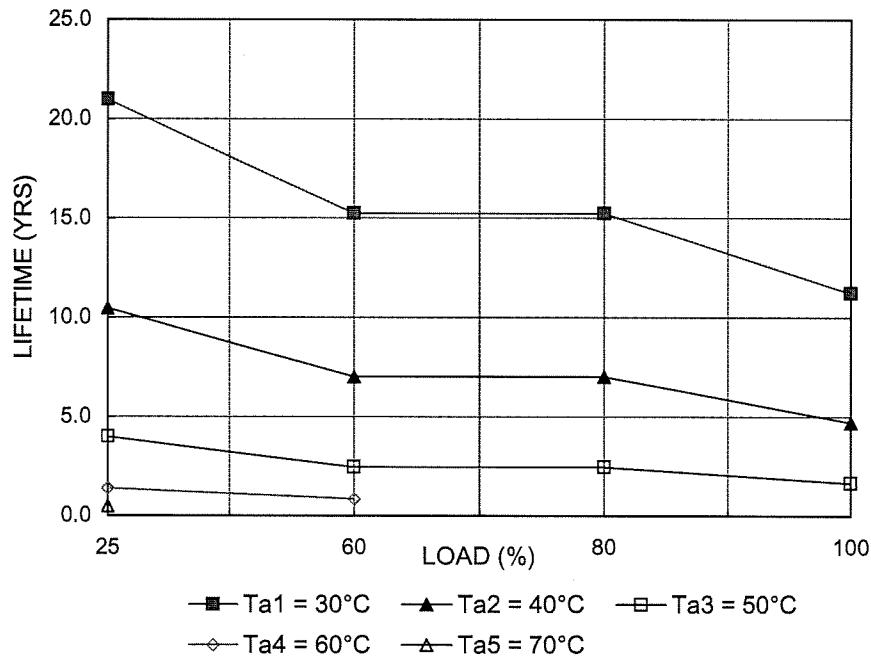
MOUNTING : D

VIN : 200VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	21.0	10.5	4.0	1.4	0.5
60	15.3	7.0	2.5	0.9	
80	15.3	7.0	2.5		
100	11.2	4.7	1.7		

GRAPH OF ELECTROLYTIC CAPACITOR LIFETIME VS LOAD
MOUNTING D KWD10-1212



計算式 FORMULA

- | | |
|--|--|
| 1. アルミ電解コンデンサ
AL. Electrolytic capacitor
$L = Lo \times 2^{(105-Tc)/10}$ | L : 電解コンデンサ推定寿命計算値
Elec. Capacitor computed life.
(24時間連続稼動、365日)
(24 hrs per day, 365 days per year) |
| 2. OSコンデンサ
O.S capacitor
$L = Lo \times 10^{(105-Tc)/22}$ | Lo : 電解コンデンサ保証寿命値
Guarantee life for Elec. cap.
Tc : 電解コンデンサのケース温度
Case temperature of Elec. cap. |

ELECTROLYTIC CAPACITOR LIFETIME VERSUS LOAD

MODEL : KWD10-1212

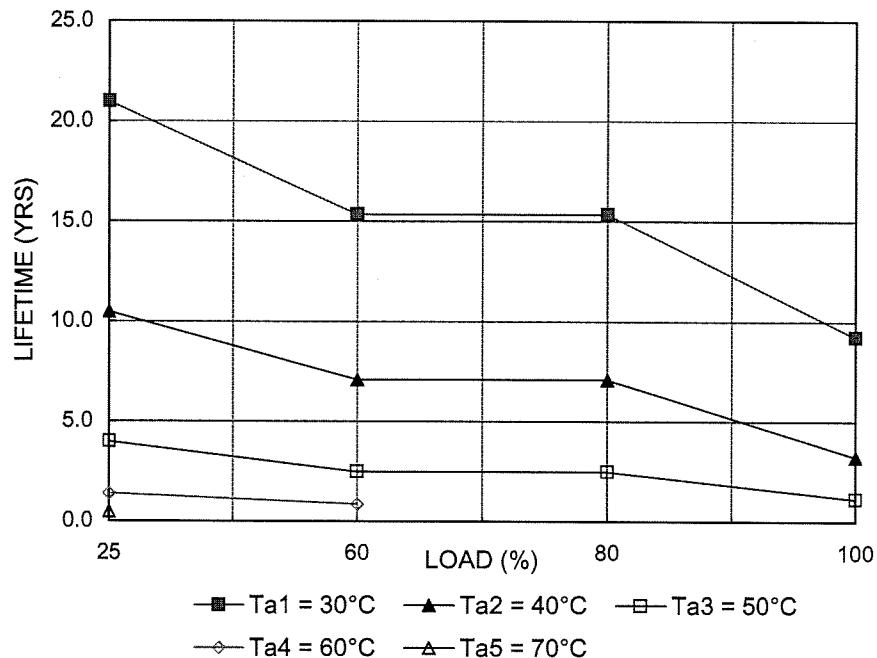
MOUNTING : E

VIN : 200VAC

DATE: SEPT 12, 2008

LOAD (%)	LIFETIME (YRS)				
	Ta = 30°C	Ta = 40°C	Ta = 50°C	Ta = 60°C	Ta = 70°C
25	21.0	10.5	4.0	1.4	0.5
60	15.4	7.1	2.5	0.9	
80	15.4	7.1	2.5		
100	9.2	3.2	1.1		

GRAPH OF ELECTROLYTIC CAPACITOR LIFETIME VS LOAD
MOUNTING E KWD10-1212



計算式 FORMULA

- | | |
|--|--|
| 1. アルミ電解コンデンサ
AL. Electrolytic capacitor
$L = Lo \times 2^{(105-Tc)/10}$ | L : 電解コンデンサ推定寿命計算値
Elec. Capacitor computed life.
(24時間連続稼動、365日)
(24 hrs per day, 365 days per year) |
| 2. OSコンデンサ
O.S capacitor
$L = Lo \times 10^{(105-Tc)/22}$ | Lo : 電解コンデンサ保証寿命値
Guarantee life for Elec. cap.
Tc : 電解コンデンサのケース温度
Case temperature of Elec. cap. |

MODEL : KWD10-1212		ABNORMAL TESTING		TEST CONDITIONS		APPROVED BY TESTED BY			
				LOAD = 100%		Vin = 200VAC Ta = 25°C		QCNEO 27/01/93 <u>M. M. M.</u>	
		TEST MODE						NOTE	
PART NO.	TEST MODE	S O F	S B	R D F	O O N	N C T	O R N	E E O	G S O
H P I M M S B	D - G	Y	Y	O U M E A	O O O	C H H	T O T	K E S	T O D
O E R O R E	D - S	Y	Y	D M E D M	C V U	H A E			
R N E K K S L	G - S	Y	Y	A E L H G O	L P P	N R G			
T E E T L	D	Y	Y	T Q E W .	. U	S E			
A B				T N					
1 MOSFET Q1	D - G	Y	Y						
2 2SK1510-01L	D - S	Y	Y						
3	G - S	Y	Y						
4	D	Y	Y						
5	S	Y	Y						
6	G	Y	Y						
7									
8 TRANSISTOR Q2	C - E	Y	Y						
9 2SC2873-Y-TE12L	C - B	Y	Y						
10	B - E	Y	Y						
11	C	Y	Y						
12	E	Y	Y						
13	B	Y	Y						
14									
15 I.C. A1	1 - 2	Y	Y						
16 UC2842ADW	2 - 3	Y	Y						
17	3 - 4	Y	Y						
18	4 - 5	Y	Y						
19	5 - 6	Y	Y						
20	6 - 7	Y	Y						
21	7 - 8	Y	Y						
22	9 - 10	Y	Y						
23	10 - 11	Y	Y						
24	11 - 12	Y	Y						
25									

*** A : SLIGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10-1212		ABNORMAL TESTING										TEST CONDITIONS		TESTED	
		LOAD = 100%										Vin = 200VAC Ta = 25°C		CCNED 1/10.3/9.3 <u>lambda</u>	
PART NO.	TEST MODE	S	O	F	S	S	B	R	D	F	O	N	O	R	N
		H	P	I	M	M	B	E	A	U	O	O	C	E	
1	A1	12-13	Y												
2		13-14	Y												
3		14-15	Y												
4		15-16	Y												
5		1	Y												
6		2	Y												
7		3	Y												
8		4	Y												
9		5	Y												
10		6	Y												
11		7	Y												
12		8	Y												
13		9	Y												
14		10	Y												
15		11	Y												
16		12	Y												
17		13	Y												
18		14	Y												
19		15	Y												
20		16	Y												
21															
22															
23															
24															
25															

*** A : SUGHT B : PROLONGED

TDK-Lambda

TDK-Lambda

MODEL : KWD10-1212		ABNORMAL TESTING												TEST CONDITIONS		DWG NO: PA774-57-04	
														APPROVED TESTED			
														Vin = 200VAC Ta = 25°C		CCNEO 1.7A3/03 <i>lambda</i>	
PARTS NAME	PART NO.	TEST MODE	S	O	F	S	S	B	S	R	D	F	O	O	N	O	
1 SHUNT REGULATOR	A2	K-A	Y														
2 HA17431UA-TL		K-R	Y														
3		R-A	Y														
4		K	Y														
5		A	Y														
6		R	Y														
7																	
8 PHOTO COUPLER	PC1	1-2	Y														
9 TLP121GR-TPL		4-6	Y														
10		1	Y														
11		3	Y														
12		4	Y														
13		6	Y														
14																	
15 CHIP BRIDGE	D1	AC	Y														
16 S1WB(A)60B	D1	AC	Y														
17	D1	DC	Y														
18	D1	DC	Y														
19																	
20																	
21 CHIP DIODE	D2	A-K	Y														
22 EC8FS6-TE12L		A-K	Y														
23																	
24 1SS184-TE85L	D3	A-K	Y														
25		A-K	Y														

*** A : SIGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10-1212		ABNORMAL TESTING												TEST CONDITIONS		DWG NO: PA774-57-05	
														LOAD = 100%		APPROVED TESTED	
														Vin = 200VAC		CENCO 1/76.3/93	
PARTS NAME	PART NO.	TEST MODE												NOTE	R N E O O T K E S O T O D	R N E O O T K E S O T O D	
1	1SS184-TE85L	D4	A-K	Y										Y	Y		
2			A-K	Y										Y	Y		
3																	
4	CHIP DIODE	D5	A-K	Y										Y	Y		
5	D1FL20U		A-K	Y										Y	Y		
6																	
7	CHIP DIODE	D6	A-K	Y										Hiccup	Y		
8	D1FL20U		A-K	Y										Y	Y		
9																	
10	CHIP DIODE	D7	A-K	Y										Y	Y		
11	D1FL20U		A-K	Y										Y	Y		
12																	
13	NOT ASSIGNED	D8															
14																	
15																	
16	NOT ASSIGNED	D9															
17																	
18																	
19	CHIP DIODE	D10	A-K	Y										Hiccup	Y		
20	D1FL20U		A-K	Y										Y	Y		
21																	
22	CHIP DIODE	D11	A-K	Y										Hiccup	Y		
23	D1FL20U		A-K	Y										Y	Y		
24																	
25																	

*** A : SUGHT B : PROLONGED

~~22~~ / 40

*** A : SUGGI B : PROLONGED

TDK-Lambda

23
40

MODEL : KWD10-1212		ABNORMAL TESTING		TEST CONDITIONS		APPROVED	TESTED
	PARTS NAME	PART NO.	TEST MODE	LOAD = 100%	Vin = 200VAC	Ta = 25°C	LRCNFO 1.5/0.3/9.3 <i>Wolfin</i>
1	CAP. FILM	C1	Y				Y
2	MKC-S683M		Y				Y
3							
4	CAP. CERAMIC	C2	Y				Y
5	ECKDNS101MB		Y				Y
6							
7	NOT ASSIGNED	C3					
8							
9							
10	CAP. CERAMIC	C4	Y				Y
11	DE7100F222MVA1N		Y				Y
12							
13	CAP. CERAMIC	C5	Y				Y
14	DE7100F222MVA1N		Y				Y
15							
16	CAP. ELECT	C6	Y				Y
17	LXA400VBSN-47(M)		Y				Y
18							
19	CHIP CAP. CERAMIC	C7	Y				Y Hiccup
20	GR43-2W5R103K500FT		Y				Y
21							
22	CHIP CAP. CERAMIC	C8	Y				Y
23	C3216X7R1E34KT		Y				Y
24							
25	NOT ASSIGNED	C9					

*** A : SUGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10-1212		ABNORMAL TESTING		TEST CONDITIONS		APPROVED		TESTED	
				LOAD = 100%		Vin = 200VAC Ta = 25°C		CCNEO 1.5/03/23	
		TEST MODE							
PARTS NAME	PART NO.	S O F I M W U M S B R D F O O N O C T R N E R O R E K K S L A E L C V O O H H A E G S						R N E O T G S O T O D	
1 CHIP CAP. CERAMIC	C10	Y							Y
2 C55Y5U1E186Z-TE12		Y							Y
3									
4 CHIP CAP. CERAMIC	C11	Y							Y
5 C2012X7R1E104KT		Y							Y
6									
7 CHIP CAP. CERAMIC	C12	Y							Y
8 C3225COG1H332JT		Y							
9									
10 CHIP CAP. CERAMIC	C13	Y							Y
11 C2012COG1H221KT		Y							Y
12									
13 CHIP CAP. CERAMIC	C14	Y							Y
14 C2012X7R1H104KT		Y							Y
15									
16 CHIP CAP. CERAMIC	C15	Y							Y
17 C2012COG1H101KT		Y							
18									
19									
20 CHIP CAP. CERAMIC	C16	Y							Y
21 CM21W5R471K200BT		Y							Y
22									
23 CHIP CAP. CERAMIC	C17	Y							Y
24 C25Y5U1E106Z		Y							Y
25									

*** A : SLIGHT B : PROLONGED

TDK-Lambda

25
40

*** A : SUGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10-1212		ABNORMAL TESTING										TEST CONDITIONS		APPROVED		TESTED						
												LOAD = 100%		Vin = 200VAC		Ta = 25°C						
		TEST MODE																				
PARTS NAME	PART NO.	S	O	F	S	S	B	S	R	D	F	O	O	N	O	R	N	E	O	T	G	
		H	P	I	M	M	U	M	E	A	U	O	O	O	C	T	O	K	S	T	O	
1	CHIP RESISTOR	R1																				
2	ERJ8GEYJ304V																					
3																						
4	CHIP RESISTOR	R2																				
5	ERJ8GEYJ304V																					
6																						
7	CHIP RESISTOR	R3																				
8	ERJ8GEYJ304V																					
9																						
10	METAL O. RESISTOR	R4																				
11	ERG1SJ-623																					
12																						
13	METAL O. RESISTOR	R5																				
14	ERG1SJ-623																					
15																						
16	CHIP RESISTOR	R6																				
17	ERJ8GEYJ823V																					
18																						
19	CHIP RESISTOR	R7																				
20	ERJ8GEYJ823V																					
21																						
22	CHIP RESISTOR	R8																				
23	ERJ8GEYJ823V																					
24																						
25																						

*** A : SUGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10-1212		TEST CONDITIONS		APPROVED		TESTED	
		LOAD = 100%		Vin = 200VAC		CCNEO 15703/93	
		TEST MODE		NOTE			
PARTS NAME	PART NO.	S O H P I M R O K E E A D M S B U R E T L A E L G O W N T O E N	R D F C V P P .	O O O O C T H A E P N R G S	O O C T H A E P N R G S	R N E O K E S O T O D	
1 CHIP RESISTOR ERJ8GEYJ823V	R9	Y				Y	Y
2			Y			Y	Y
3							
4 CHIP RESISTOR ERJ8GEYJ100V	R10	Y				Y	Y
5			Y			Y	Y
6							
7 CHIP RESISTOR ERJ8GEYJ563V	R11	Y		Y		Y	Y
.8			Y			Y	Y
9							
10 CHIP RESISTOR ERJ8GEYJ322V	R12	Y	-			Y	Y
11			Y			Y	Y
12							
13 CHIP RESISTOR ERJ8GEYJ101V	R13	Y				Y	Y
14			Y			Y	Y
15							
16 CHIP RESISTOR CR1/10W2211DV	R14	Y				Y	Y
17			Y			Y	Y
18							
19 CHIP RESISTOR CR1/10W152JV	R15	Y				Y	Y
20			Y			Y	Y
21							
22 CHIP RESISTOR CR1/10W331JV	R16	Y				Y	Y
23			Y			Y	Y
24							
25							

*** A : SLIGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10 - 1212		ABNORMAL TESTING										TEST CONDITIONS		APPROVED		TESTED	
		LOAD = 100%										Vin = 200VAC Ta = 25°C		RCN EO 1/703/93		<u>Not tested</u>	
	PARTS NAME	PART NO.	TEST MODE	S	O	F	S	S	R	D	F	O	O	N	O	R	
			H	P	I	M	M	B	A	U	S	C	O	C	E		
1	CHIP RESISTOR	R17	Y														
2	ERJ8GEYJ100V		Y														
3																	
4	CHIP RESISTOR	R18	Y														
5	ERJ8GEYJ510V		Y														
6																	
7	CHIP RESISTOR	R19	Y														
8	CR1/10W102JV		Y														
9																	
10	CHIP RESISTOR	R20	Y														
11	ERJ8GEYJ300V		Y														
12																	
13	CHIP RESISTOR	R21	Y														
14	ERJ8GEYJ300V		Y														
15																	
16	CHIP RESISTOR	R22	Y														
17	ERJ8GEYJ300V		Y														
18																	
19	CHIP RESISTOR	R23	Y														
20	CR1/10W183JV		Y														
21																	
22	CHIP RESISTOR	R24	Y														
23	ERJ8GEYJ4RTV		Y														
24																	
25																	

*** A : SUGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10-1212		ABNORMAL TESTING												TEST CONDITIONS		APPROVED		TESTED	
														LOAD = 100%		Vin = 200VAC		CC/ECO	
														Ta = 25°C		1703/93		Handwritten Signature	
PARTS NAME	PART NO.	TEST MODE	S	O	F	S	S	B	R	D	F	O	O	N	O	NOTE	R	N	
1 CHIP RESISTOR	R25	Y	H	P	I	M	M	U	M	E	A	U	C	T	O	E	O		
2 ERJ8GEYJ4R7V		Y	O	E	R	O	O	R	E	D	M	S	V	H	K	E	G		
3			R	N	E	K	K	S	L	A	E	L	.	T	A	S	O		
4 CHIP RESISTOR	R26	Y	E	E	K	E	E	T	L	H	G	O	P	P	N	T	O		
5 ERJ8GEYJ4R7V		Y	T	T	T	T	T	T	T	O	E	W	.	U	R	T	D		
6																			
7 CHIP RESISTOR	R27	Y																	
8 ERJ8GEYJ150V		Y																	
9																			
10 CHIP RESISTOR	R28	Y																	
11 ERJ8GEYJ150V		Y																	
12																			
13 CHIP RESISTOR	R29	Y																	
14 ERJ8GEYJ150V		Y																	
15																			
16 CHIP RESISTOR	R30	Y																	
17 ERJ8GEYJ150V		Y																	
18																			
19 CHIP RESISTOR	R31	Y													Hiccup				
20 ERJ8GEYJ132V		Y																	
21																			
22 CHIP RESISTOR	R32	Y													Hiccup				
23 ERJ8GEYJ132V		Y																	
24																			
25																			

*** A : SUGHT B : PROLONGED

TDK-Lambda

TDK-Lambda

MODEL : KWD10-1212		ABNORMAL TESTING												TEST CONDITIONS		DWG NO: PA774-57-14	
														APPROVED TESTED			
														Vin = 200VAC Ta = 25°C		CCNFO 1.76±9.3	
		TEST MODE	PART NO.	PART NAME	S	O	F	S	S	B	R	D	F	O	O	N	O
1	CHIP RESISTOR	R33			H	P	I	M	M	U	M	E	A	U	O	O	C
2	ERJ8GEYJ150V				O	E	R	O	O	R	E	D	W	S	C	T	N
3					R	N	E	K	K	L	A	E	L	C	H	E	O
4	CHIP RESISTOR	R34			T	E	K	E	E	T	L	G	O	P	T	A	G
5	ERJ8GEYJ150V																O
6																	T
7	CHIP RESISTOR	R35															K
8	ERJ8GEYJ150V																S
9																	T
10	CHIP RESISTOR	R36															D
11	ERJ8GEYJ150V																
12																	
13	CHIP RESISTOR	R37															
14	ERJ8GEYJ132V																
15																	
16	CHIP RESISTOR	R38															
17	ERJ8GEYJ132V																
18																	
19	CHIP RESISTOR	R39															
20	ERJ8GEYJ621V																
21																	
22	CHIP RESISTOR	R40															
23	CR1/10W222JV																
24																	
25																	

*** A : SIGHT B : PROLONGED

MODEL : KW1D10-1212		ABNORMAL TESTING		TEST CONDITIONS		DWG NO: PA774-57-15	
				LOAD = 100%		APPROVED TESTED	
						<i>CCNEO</i>	<i>1/1/0193</i>
PARTS NAME	PART NO.	TEST MODE				NOTE	
		S O F S R D F O O N O C T R N E O R E D M S B C U O O H A E R G S				R N E O T K E G S O T O D	
1 CHIP RESISTOR	R41	Y					
2 CR1/10W682JV		Y				Y Stability problem; High pitch sound	Y
3							
4 CHIP RESISTOR	R42	Y					
5 CR1/10W1742DV		Y					
6							
7 CHIP RESISTOR	R43	Y					
8 CR1/10W2001DV		Y					
9							
10 TRANSFORMER	T1	1-2	Y			Y Hiccup	Y
11 PA77401		3-4	Y				
12		6-7	Y				
13		6-8	Y				
14		7-8	Y				
15		1	Y				
16		2	Y				
17		3	Y				
18		4	Y				
19		6	Y			ZD1 shorted	Y
20		7	Y			Y Vout unstable	Y
21		8	Y			ZD1 shorted	Y
22							
23							
24							
25							

*** A : SUGHT B : PROLONGED

TDK-Lambda

MODEL : KWD10-1212		TEST MODE		TEST CONDITIONS		DWG NO: PA774-57-16	
		ABNORMAL TESTING		LOAD = 100%		APPROVED TESTED	
				Vin = 200V/AC Ta = 25°C		CCNEO 1/76.3/93	
PART NAME	PART NO.	S O F I M M S B S A D F O O N O C T H A E R N E R O R K S L E L M E A U M E D M S B C V O O O C T H A E R N G S E	NOTE	R N E E O T E G S O T O D			
1 BALUN COIL	L1	1-2 Y				Y	
2 UF1717H-103YR25-01		3-4 Y				Y	
3		1 Y				Y	
4		2 Y				Y	
5		3 Y				Y	
6		4 Y				Y	
7							
8 CHIP COIL	L4	Y				Y	
9 LQH3C2R2M04		Y				Y	
10							
11 NOT ASSIGNED	L5						
12							
13							
14 CHIP COIL	L6	Y				Y	
15 LQH3C2R2M04		Y				Y	
16							
17 NOT ASSIGNED	L7						
18							
19							
20							
21							
22							
23							
24							
25							

*** A : SUGHT B : PROLONGED

TDK-Lambda

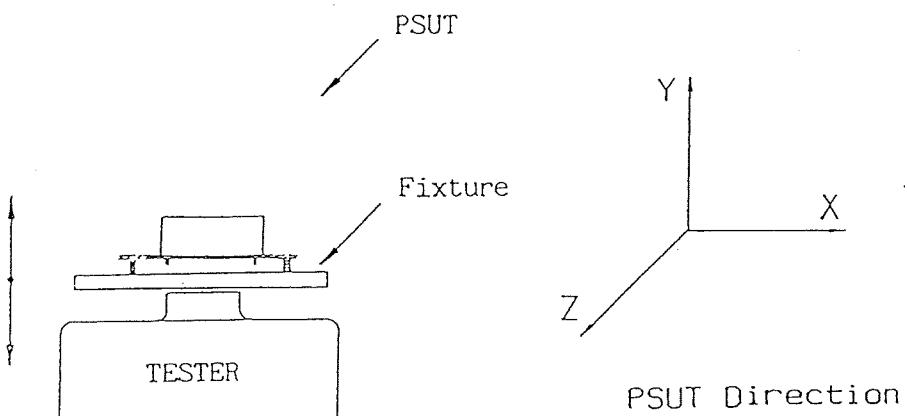
VIBRATION TEST

TYPES OF VIBRATION TEST :

- A) OSCILLATOR FREQUENCY SWEEP
- B) RESONANCE FREQUENCY

EQUIPMENT : EMIC CORPORATION VIBRATION TEST SYSTEM F-400-BM-E47
VIBRATION GENERATOR 905-FN

PROCEDURE :



VIBRATION TEST WITH FREQUENCY SWEEP

FREQUENCY	10 ~ 55 Hz.
SWEEP TIME	1 min.
ACCELERATION	MAX 10G.
AMPLITUDE	1.65mm ^{PP} CONSTANT.
DIRECTION	X, Y, Z.
DURATION	1 hr. for each direction.

TEST POINT :

1. Output voltage (Apply some shock when checking the o/p voltage, and observe any abnormalities.)
2. Ripple voltage (At AC 100V input and output)
- 3.. Mechanical Condition (No breakage)

認 APPD	<i>B. P. J.</i> 5/MAR/93	設 計 ENGR	<i>SL KWW</i> 27 - Nov - 92	図面番号 DWG-No.
検 査 CHK	<i>CCNEO</i> 30 - DEC - 92	製 図 DWG	<i>WILLIAM PHIN</i> 25 - Nov - 92	PA774-64-01

TEST RESULTS :
(after vibration)

TEST POINT	OUTPUT VOLTAGE (V)			RIPPLE VOLTAGE (mV)			(MECHANICAL CONDITION)	NOTE
	CH1	CH2	CH3	CH1	CH2	CH3		
BEFORE TEST	11.687	11.584	—	35	35	—	O.K	
DIRECT ⁿ TEST	11.692	11.588	—	35	35	—	O.K	
X	11.695	11.596	—	35	35	—	O.K	
Y	11.693	11.591	—	35	35	—	O.K	
Z	11.693	11.591	—	35	35	—	O.K	

EVALUATION RESULT :

 PASS

/ FAIL

VISUAL INSPECTION RESULT :

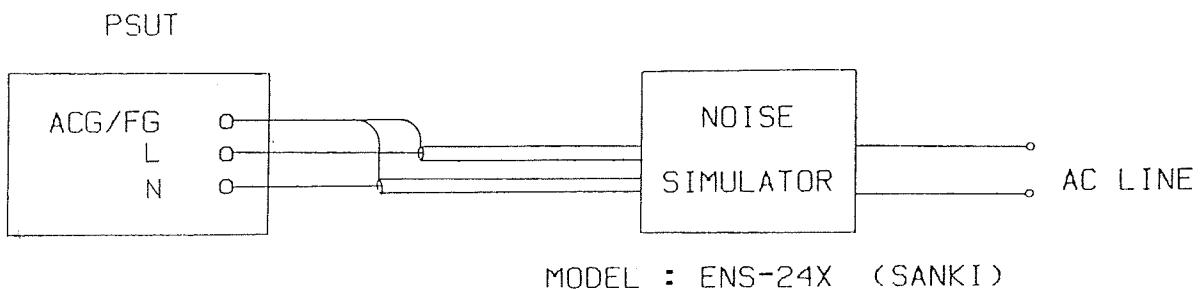
 PASS

/ FAIL

認. APPD		設計 ENGR		図面番号 DWG-No.	
.	.	.	.		
検 査 印 CHK		製 図 DWG			
.	.	.	.		

NOISE SIMULATION TEST

Circuit for measurement and equipment used :



Testing Conditions :

Input Voltage : AC100V

Output Voltage : Rated

Output Current : 0% , 100%

Ambient Temp. : 25 °C

Settings :

MODE Normal , Common

TRIG SELECT Line or Ext (Line)

PULSE WIDTH 50, 200, 800, 1000ns

PHASE SHIFT 0 ~ 360 Degree

POLARITY + , -

NOISE LEVEL 0 ~ 2KV

Acceptance Criteria :

1) No damage of PSUT

2) No output failure
(eg. Over/Uundershoot < 3% of Vo)

3) Check any abnormalities (eg. noise)

Evaluation Result :

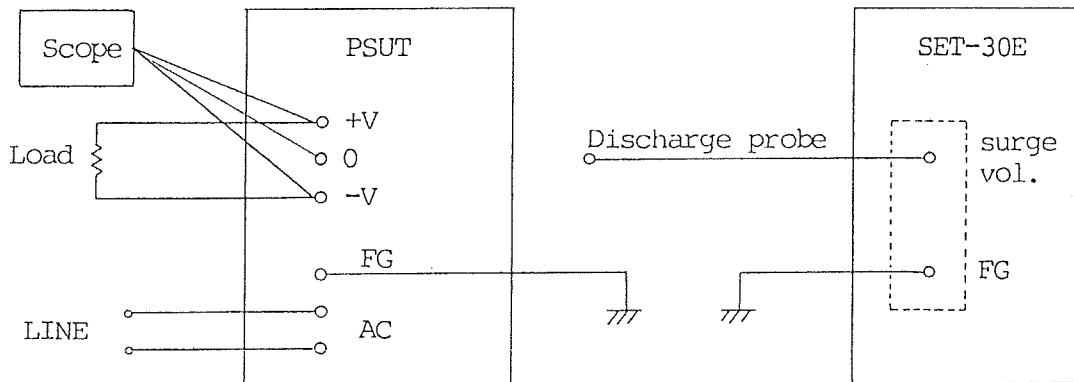


/ FAIL

認 APPD	<i>[Signature]</i> 15 MAR '93	設 計 ENGR	<i>[Signature]</i> 12. 1. 93	図面番号 DWG-No.
検 図 CH K	CCNEO 12. 01. 93	製 図 DWG	Ramem.m 12. 1. 93	PA774-61-01 - <input type="checkbox"/>

ELECTROSTATIC DISCHARGE TEST

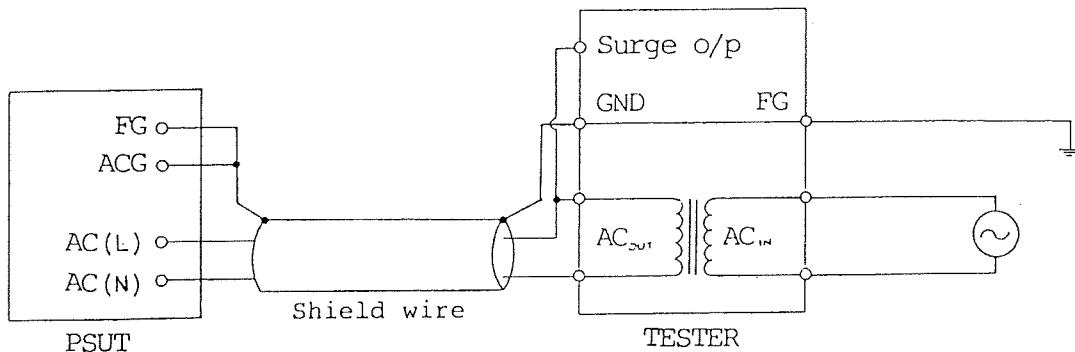
EQUIPMENT : SET-30E (SANKI ELECTRONIC)

Discharge Resistor : 250 ohm
Capacitor unit : 200 pFCONDITIONS : Ambient Temperature : 25°C
Input Voltage : AC100V
Output Voltage : Rated
Output Current : Rated
Applied Voltage : ±3kV, ±5kV, ±10kV, ±15kVPROCEDURE :
The PSUT should be in a good working condition.
Discharge the applied voltage to the touchable
parts of the PSUT (Chassis, Input Terminal,
Output Terminal, FG Terminal, ACG Terminal) and
check any abnormalities.Each point to be tested 3 times with different
polarity. Voltage should be applied from 3kV
to 15kV.ACCEPTANCE CRITERIA :
1. No damage of PSUT
2. No output failure ($\Delta V_o < 3\% \text{ of } V_o$)
3. No abnormalitiesEVALUATION RESULT : PASS / FAIL

認 APPD	<i>[Signature]</i> 15 MAR '93	設 計 ENGR	85 12 · 1 · 93	図面番号 DWG-No.
検 図 C H K	CC NEO 12 · 01 · 93	製 図 DWG	Ramam. M. 12 · 1 · 93	PA774-62-01 -

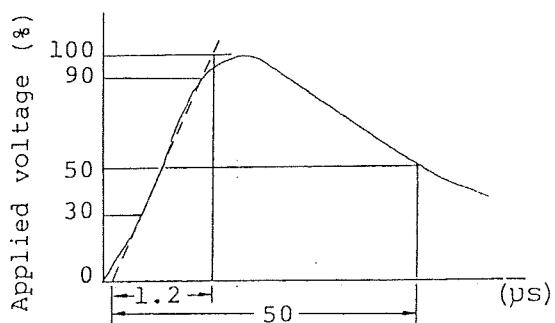
LIGHTNING SURGE TEST

TEST CIRCUIT, TEST EQUIPMENT



CONDITIONS :	Input Voltage	: AC100V
	Output Voltage	: Rated
	Output Current	: Rated
	Applied Voltage	: From 3kV in steps of 0.5kV Check the max. withstand voltage
	Applied Point	: Between FG - AC
	Number of Test	: Each voltage 3 times
	Polarity	: + , -
	Ambient Temp.	: 25°C

APPLIED VOLTAGE WAVEFORM :



- ACCEPTANCE CRITERIA :
1. No damage to the PSUT
 2. No output failure
 3. No abnormalities

EVALUATION RESULT :

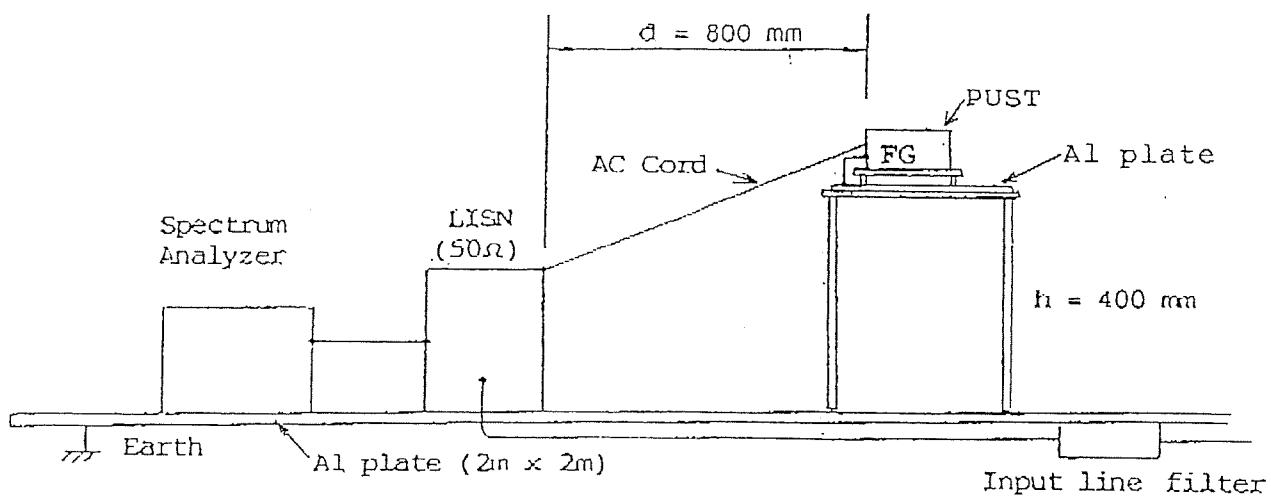
PASS
5KV

/ FAIL

認 APPD	<i>S. D. J.</i> 8 · MAR · 93	設 計 ENGR	<i>J. S.</i> 12 · 1 · 93	図面番号 DWG-No.
検 図 C H K	CC NEO. 12 · 01 · 93	製 図 DWG	Ramesh M. 12 · 1 · 93	PA774-74-01 -

EMI TEST

TEST CIRCUIT :



TEST EQUIPMENTS :

SPECTRUM ANALYZER	85688	HEWLETT PACKARD
QUASI-PEAK ADAPTER	85650A	HEWLETT PACKARD
RF PRESELECTOR	85685A	HEWLETT PACKARD
LISN	3825/2	EMCO

CONDITIONS :

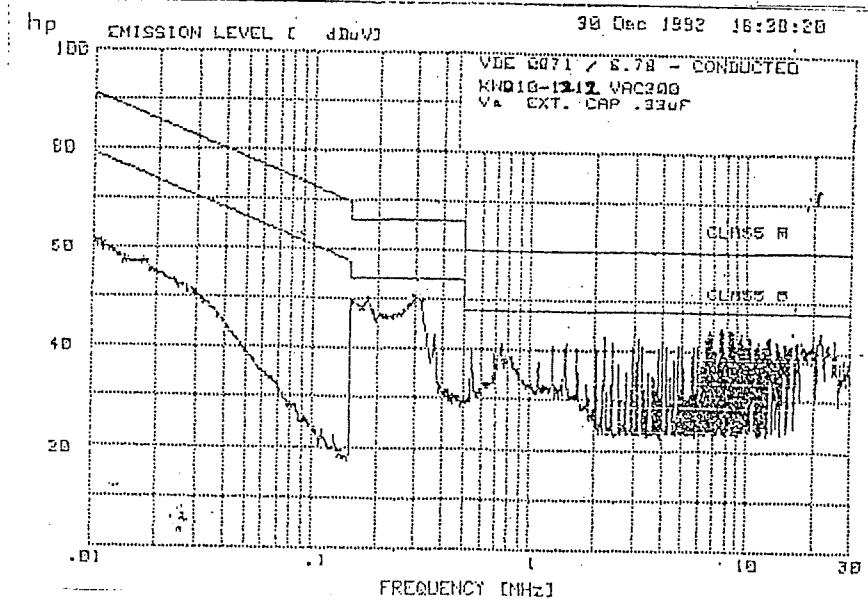
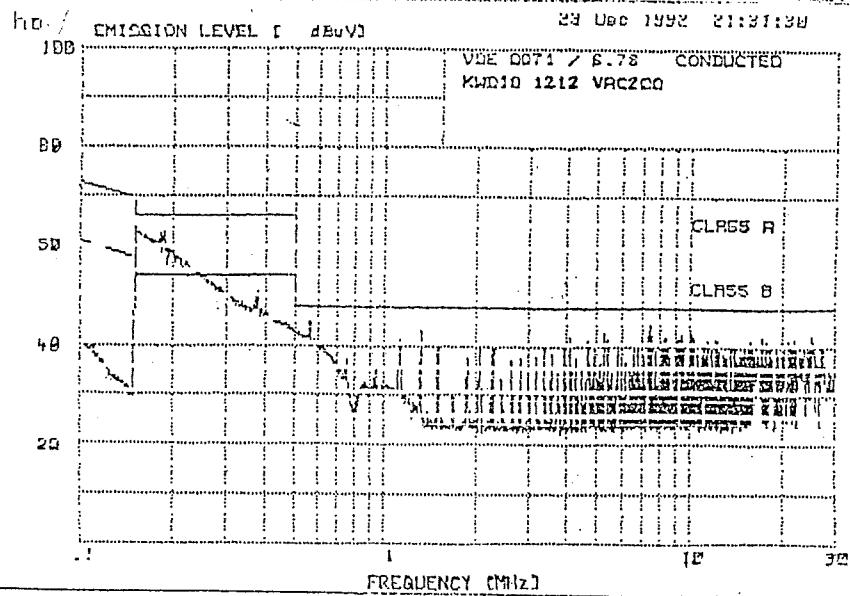
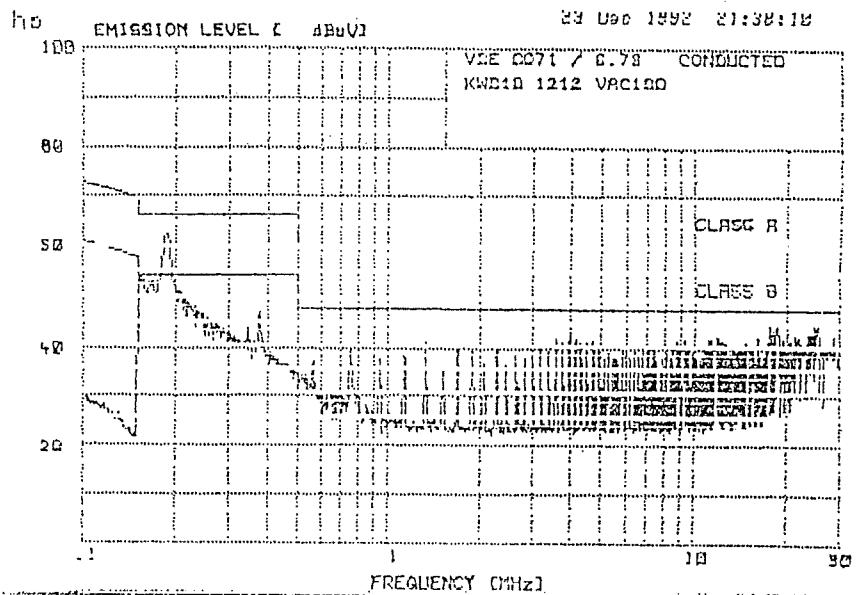
INPUT VOLTAGE	: AC100V, AC200V
OUTPUT VOLTAGE	: RATED
OUTPUT CURRENT	: RATED
AMBIENT TEMP	: 25°C

認 APPD		設計 ENGR		図面番号 DWG-No.	
検 CHK		製 DWG			

KWD 10-1212

LOAD : 100%

DATE 15 · MAR · 1993 ·



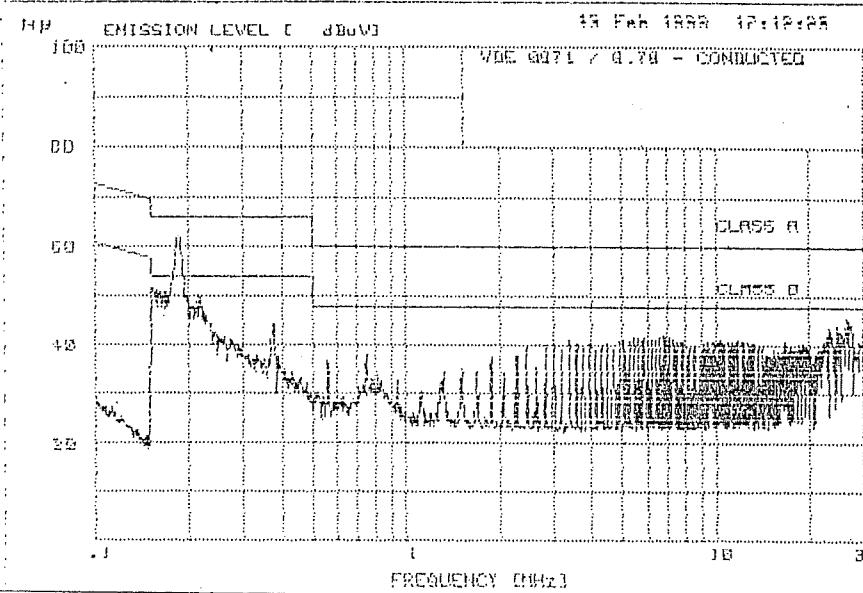
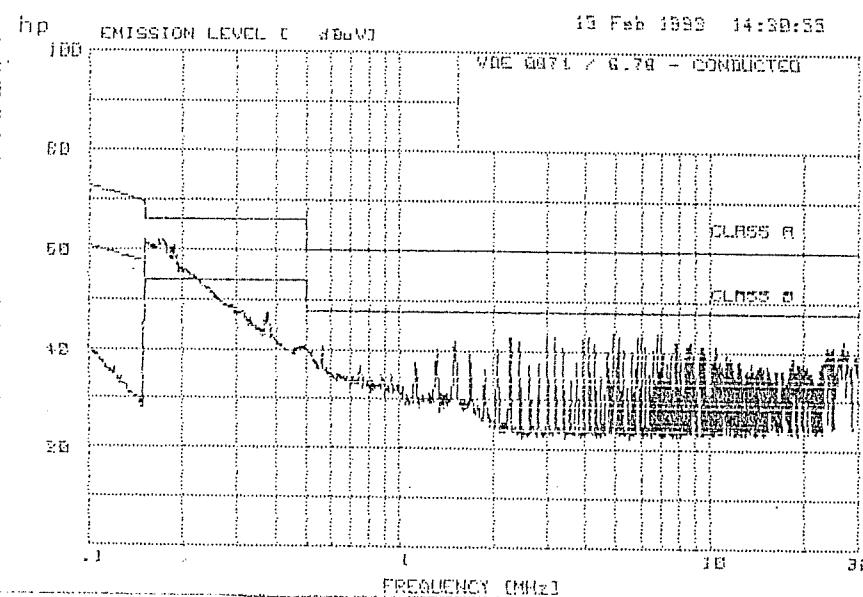
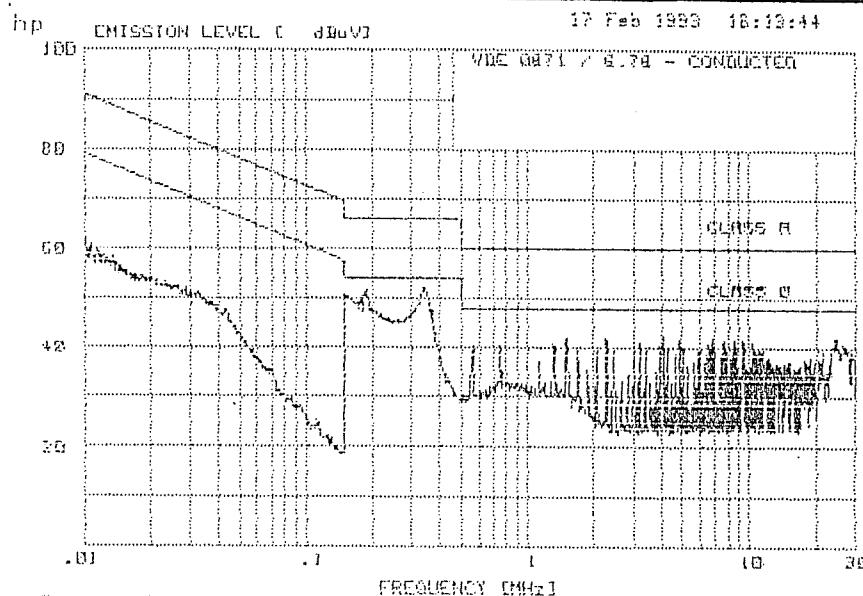
認 APPD		設計 ENGR		圖面番号 D WG-No.
.	.		.	
檢圖 C H K		製圖 D W G		PA774-70-02-

KWD 10-1515

LOAD = 100%

DATE 15 · MAR · 1993

40
40



認 APPD	.	設 ENGR	.	図面番号 DWG-No.
検 CHK	.	製 DWG	.	PA774-70-03 -
	.		.	